

L Number	Hits	Search Text	DB	Time stamp
1	652	257/415.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/14 14:05
2	585	257/419.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/14 14:05
3	38	257/424.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/14 14:05
-	161	257/254.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/05 16:14
-	9	(257/254.ccls. and (gate near3 oxide)) and acceleration	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/05 16:12
-	2	((257/254.ccls. and (gate near3 oxide)) and acceleration) and spring	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/05 16:12
-	10	257/254.ccls. and acceleration and spring	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/05 16:15
-	8	(257/254.ccls. and acceleration and spring) not ((257/254.ccls. and (gate near3 oxide)) and acceleration)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/05 16:19
-	12153	acceleration same switch	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/30 14:48
-	21	(acceleration same switch) and ((gate near5 (oxide or insulator)) and (drain or source))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/12 18:45
-	11	((acceleration same switch) and ((gate near5 (oxide or insulator)) and (drain or source))) and spring	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/05 16:21
-	24	(acceleration same switch) and (gate near5 (oxide or insulator))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/05 16:22
-	11	((acceleration same switch) and (gate near5 (oxide or insulator))) and spring	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/05 16:31
-	363	(acceleration same switch) and gate and drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/05 16:57

-	330	((acceleration same switch) and gate and drain) and source	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/05 16:58
-	312	((((acceleration same switch) and gate and drain) and source) not ((acceleration same switch) and (gate near5 (oxide or insulator)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/05 16:59
-	0	(((((acceleration same switch) and gate and drain) and source) not ((acceleration same switch) and (gate near5 (oxide or insulator)))) and spring) not (((acceleration same switch) and gate and drain) and source) not ((acceleration same switch) and (gate near5 (oxide or insulator)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/05 17:44
-	183	((((acceleration same switch) and gate and drain) and source) not ((acceleration same switch) and (gate near5 (oxide or insulator)))) not (((((acceleration same switch) and gate and drain) and source) not ((acceleration same switch) and (gate near5 (oxide or insulator)))) and spring)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/05 17:52
-	160	257/254.ccls. not ((acceleration same switch) and (gate near5 (oxide or insulator)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/05 17:53
-	15	(257/254.ccls. and (gate near3 oxide)) not (((acceleration same switch) and gate and drain) and source) not ((acceleration same switch) and (gate near5 (oxide or insulator)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/05 17:53
-	5	(US-5619050-\$ or US-5504356-\$ or US-5922212-\$ or US-6388299-\$ or US-5812427-\$).did.	USPAT	2003/02/06 13:00
-	5	(US-5619050-\$ or US-5504356-\$ or US-5922212-\$ or US-6388299-\$ or US-5812427-\$).did.	USPAT	2003/02/06 12:58
-	5	(US-5619050-\$ or US-5504356-\$ or US-5922212-\$ or US-6388299-\$ or US-5812427-\$).did.	USPAT	2003/02/06 12:58
-	1	("5619050").PN.	USPAT	2003/02/06 12:59
-	1	((US-5619050-\$ or US-5504356-\$ or US-5922212-\$ or US-6388299-\$ or US-5812427-\$).did.) and (silicon near dioxide)	USPAT	2003/02/06 13:03
-	1	((US-5619050-\$ or US-5504356-\$ or US-5922212-\$ or US-6388299-\$ or US-5812427-\$).did.) and (silicon near dioxide)	USPAT	2003/02/06 13:03
-	13	((acceleration same switch) and (gate near5 (oxide or insulator))) not (((acceleration same switch) and (gate near5 (oxide or insulator))) and spring)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/06 13:05
-	0	((((acceleration same switch) and (gate near5 (oxide or insulator))) not (((acceleration same switch) and (gate near5 (oxide or insulator))) and spring)) and (silicon near3 dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/06 13:05
-	15	257/254.ccls. and (gate near3 oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/06 13:05

-	4	(257/254.ccls. and (gate near3 oxide)) and (silicon near3 dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/30 15:29
-	129	((((acceleration same switch) and gate and drain) and source) not ((acceleration same switch) and (gate near5 (oxide or insulator)))) and spring	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/06 13:10
-	0	(((((acceleration same switch) and gate and drain) and source) not ((acceleration same switch) and (gate near5 (oxide or insulator)))) and spring) and (silicon near3 oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/06 13:11
-	1	(((((acceleration same switch) and gate and drain) and source) not ((acceleration same switch) and (gate near5 (oxide or insulator)))) and spring) and (silicon near3 dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/06 13:11
-	238	73/514.36.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/06 13:11
-	193	73/514.36.ccls. and (acceleration or pressure)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/06 13:12
-	4	(73/514.36.ccls. and (acceleration or pressure)) and gate and (silicon near3 dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/06 13:12
-	1	("5627397").PN.	USPAT	2003/02/06 14:34
-	2190	((acceleration same switch) and (semiconductor or ic or (integrated near2 circuit) or chip or die)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/30 14:50
-	1458	((acceleration same switch) and (semiconductor or ic or (integrated near2 circuit) or chip or die)) and (source or drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/12 18:34
-	167	257/254.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/30 15:29
-	818	257/417.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/30 15:29
-	243	257/418.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/30 15:30
-	157	257/420.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/14 14:05
-	103	73/514.21.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/30 15:30

-	1508	((acceleration same switch) and (semiconductor or ic or (integrated near2 circuit) or chip or die)) and (source or drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 18:35
-	26	(acceleration same switch) and ((gate near5 (oxide or insulator)) and (drain or source))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 18:45